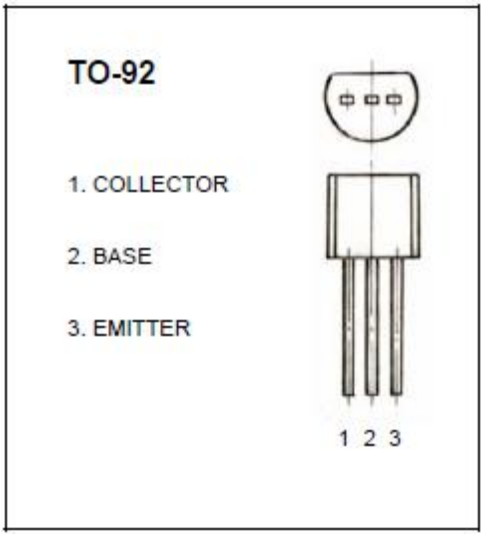
isc Silicon NPN Transistor BC548



DESCRIPTION

- High Voltage
- Complement to Type BC558
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- For TV and home appliance equipment.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	100	mA
P_C	Collector Power Dissipation @T_C=25℃	500	mW
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C=100 μ A; I_E= 0	30			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 2mA; I_B= 0	30			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 100 μ A; I_C= 0	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 100mA ; I_B= 5mA			0.6	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 100mA ; I_B= 5mA			0.9	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 30V; I_E= 0			0.1	μ A
I_{CEO}	Collector Cutoff Current	V_{CE}= 30V; I_B= 0			0.1	μ A
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			0.1	μ A
h_{FE}	DC Current Gain	I_C= 2mA ; V_{CE}= 5V	110		800	

◆ **h_{FE} Classifications**

BC548A	BC548B	BC548C
110-220	200-450	420-800